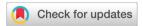
Nanoscale



CORRECTION

View Article Online



Cite this: Nanoscale, 2017, 9, 12196

Correction: Broadband ultrafast photovoltaic detectors based on large-scale topological insulator Sb₂Te₃/STO heterostructures

Honghui Sun,^a Tian Jiang,*^{a,b,c,d} Yunyi Zang,^c Xin Zheng,^{a,d} Yan Gong,^c Yong Yan,^e Zhongjie Xu,^{b,d} Yu Liu,^b Liang Fang,*^{a,d} Xiang'ai Cheng^{b,d} and Ke He^c

DOI: 10.1039/c7nr90164j

rsc.li/nanoscale

Correction for 'Broadband ultrafast photovoltaic detectors based on large-scale topological insulator Sb₂Te₃/STO heterostructures' by Honghui Sun, *et al.*, *Nanoscale*, 2017, **9**, 9325–9332.

The authors have noticed an error in the published version of this manuscript. The sentence beginning "Due to the difference in doping concentration between Sb₂Te₃ ($N_h \sim 2$ synth 10^{19} cm⁻³)..." should be corrected to "Due to the difference in doping concentration between Sb₂Te₃ ($N_h \sim 2 \times 10^{19}$ cm⁻³)..."

In the revised sentence, the word "synth" has been changed to "x".

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aState Key Laboratory of High Performance Computing, College of Computer, National University of Defense Technology, Changsha 410073, China. E-mail: tjiang@nudt.edu.cn

^bCollege of Optoelectronic Science and Engineering, National University of Defense Technology, Changsha 410073, China

^cState Key Laboratory of Low-Dimensional Quantum Physics, Department of Physics, Tsinghua University, Beijing 100084, China

^dInterdisciplinary Center of Quantum Information, National University of Defense Technology, Changsha 410073, China

eHenan Key Laboratory of Photovoltaic Materials, College of Physics and Materials Science, Henan Normal University, Xinxiang 453007, China